SN74AHCT595-Q1 Automotive 8-Bit Shift Registers With 3-State Output Registers

1 Features

- AEC-Q100 qualified for automotive applications:
  - Device temperature grade 1: -40°C to +125°C
  - Device HBM ESD classification level 2
  - Device CDM ESD classification level C4B
- Available in wettable flank QFN package
- Operating range 4.5V to 5.5V V_{CC}
- TTL-Compatible inputs
- Low delay, 6ns typ (25°C, 5V)
- Latch-up performance exceeds 250mA per JESD 17

2 Applications

- Network switches
- Power infrastructures
- PCs and notebooks
- LED displays
- Servers

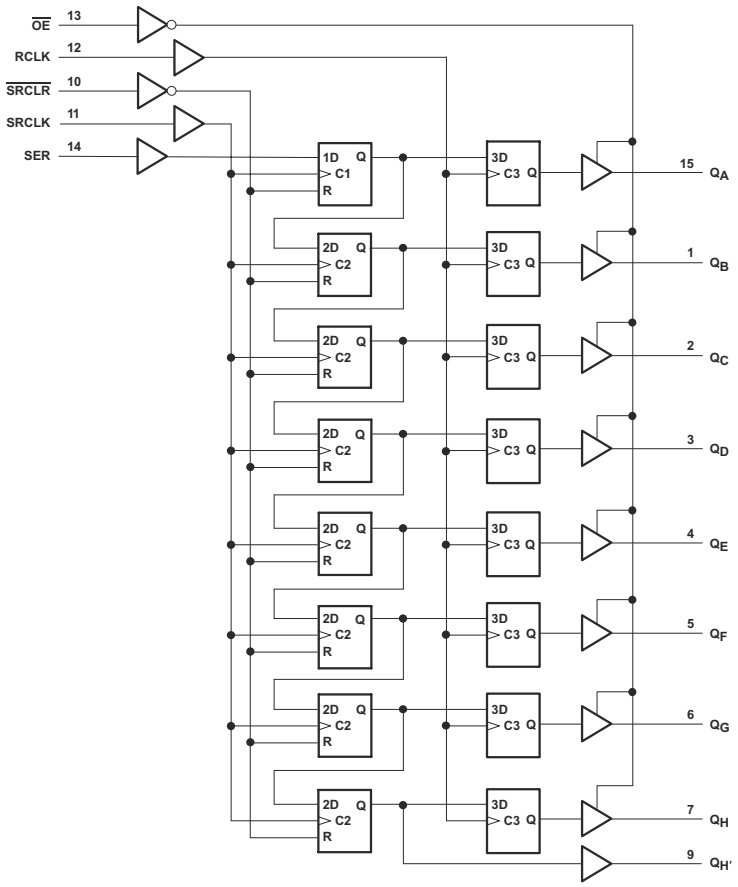
3 Description

The SN74AHCT595-Q1 devices contain an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. Both the shift register clock (SRCLK) and storage register clock (RCLK) are positive-edge triggered.

Package Information

PART NUMBER	PACKAGE(1)	PACKAGE SIZE(2)	BODY SIZE (NOM)(3)
SN74AHCT595-Q1	BQB (WQFN, 16)	3.5mm × 2.5mm	3.5mm × 2.5mm
	PW (TSSOP, 16)	5.0mm × 6.4mm	5.0mm × 4.4mm

(1) For more information, see Section 11.
(2) The package size (length × width) is a nominal value and includes pins, where applicable.
(3) The body size (length × width) is a nominal value and does not include pins.



Pin numbers shown are for the PW and BQB packages.

Simplified Schematic

Table of Contents

1 Features....1
2 Applications....1
3 Description....1
4 Pin Configuration and Functions....3
5 Specifications....4
5.1 Absolute Maximum Ratings....4
5.2 ESD Ratings....4
5.3 Recommended Operating Conditions....4
5.4 Thermal Information....4
5.5 Electrical Characteristics....5
5.6 Timing Characteristics....5
5.7 Switching Characteristics....6
5.8 Noise Characteristics....6
5.9 Typical Characteristics....7
6 Parameter Measurement Information....8
7 Detailed Description....9
7.1 Overview....9
7.2 Functional Block Diagram....9
7.3 Feature Description....10
7.4 Device Functional Modes....12
8 Application and Implementation....13
8.1 Application Information....13
8.2 Typical Application....13
8.3 Power Supply Recommendations....14
8.4 Layout....14
9 Device and Documentation Support....16
9.1 Documentation Support....16
9.2 Receiving Notification of Documentation Updates....16
9.3 Support Resources....16
9.4 Trademarks....16
9.5 Electrostatic Discharge Caution....16
9.6 Glossary....16
10 Revision History....16
11 Mechanical, Packaging, and Orderable Information....16

4 Pin Configuration and Functions

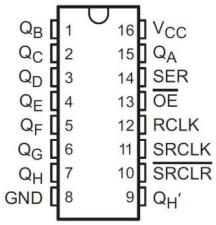


Figure 4-1.
SN74AHCT595-Q1 PW Package (Top View)

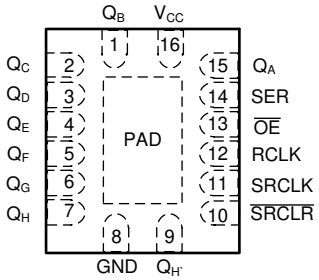


Figure 4-2. SN74AHCT595-Q1 BQB Package, 16-Pin WQFN (Top View)

Table 4-1. Pin Functions

PIN		TYPE[1]	DESCRIPTION
NAME	NO.		
Q_B	1	O	Q_B Output
Q_C	2	O	Q_C Output
Q_D	3	O	Q_D Output
Q_E	4	O	Q_E Output
Q_F	5	O	Q_F Output
Q_G	6	O	Q_G Output
Q_H	7	O	Q_H Output
GND	8	—	Ground Pin
$Q_{H'}$	9	O	$Q_{H'}$ Output
$\overline{SRCLR}$	10	I	$\overline{SRCLR}$ Input
SRCLK	11	I	SRCLK Input
RCLK	12	I	RCLK Input
$\overline{OE}$	13	I	Output Enable
SER	14	I	SER Input
Q_A	15	O	Q_A Output
V_{CC}	16	—	Power Pin
Thermal Pad[2]		—	The thermal pad can be connected to GND or left floating. Do not connect to any other signal or supply.

(1) I = input, O = output
(2) BQB package only

5 Specifications

5.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)(1)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		–0.5	7	V
V_I	Input voltage range(2)		–0.5	7	V
V_O	Voltage range applied to any output in the high-impedance or power-off state(2)		–0.5	7	V
V_O	Output voltage range(2)		–0.5	V_{CC} + 0.5	V
I_{IK}	Input clamp current	V_I < -0.5V		-20	mA
I_{OK}	Output clamp current	V_O < -0.5V or V_O > V_{CC} + 0.5V		±20	mA
I_O	Continuous output current	V_O = 0 to V_{CC}		±25	mA
	Continuous output current through V_{CC} or GND			±75	mA
T_J	Junction temperature			150	°C
T_{stg}	Storage temperature		-65	150	°C

(1) Operation outside the *Absolute Maximum Ratings* may cause permanent device damage. Absolute maximum ratings do not imply functional operation of the device at these or any other conditions beyond those listed under *Recommended Operating Conditions*. If briefly operating outside the *Recommended Operating Conditions* but within the *Absolute Maximum Ratings*, the device may not sustain damage, but it may not be fully functional. Operating the device in this manner may affect device reliability, functionality, performance, and shorten the device lifetime.
(2) The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

5.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per AEC Q100-002 HBM ESD Classification Level 2(1)	±2000	V
		Charged device model (CDM), per AEC Q100-011 CDM ESD Classification Level C4B	±1000	

(1) AEC Q100-002 indicate that HBM stressing shall be in accordance with the ANSI/ESDA/JEDEC JS-001 specification.

5.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

Specification	Description	Condition	MIN	MAX	UNIT
V_{CC}	Supply voltage		4.5	5.5	V
V_{IH}	High-level input voltage	V_{CC} = 5V	2		V
V_{IL}	Low-Level input voltage	V_{CC} = 5V		0.8	V
V_I	Input Voltage		0	5.5	V
V_O	Output Voltage		0	V_{CC}	V
I_{OH}	High-level output current	V_{CC} = 5V ± 0.5V		-8	mA
I_{OL}	Low-level output current	V_{CC} = 5V ± 0.5V		8	mA
$\Delta t/\Delta v$	Input transition rise or fall rate	V_{CC} = 5V ± 0.5V		20	ns/V
T_A	Operating free-air temperature		–40	125	°C

5.4 Thermal Information

THERMAL METRIC(1)		WBQB (WQFN)	PW (TSSOP)	UNIT
		16 PINS	16 PINS	
$R_{\theta JA}$	Junction-to-ambient thermal resistance	105.6	135.9	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	96.6	70.3	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	75.4	81.3	°C/W

5.4 Thermal Information (continued)

THERMAL METRIC[1]		WBQB (WQFN) 16 PINS	PW (TSSOP) 16 PINS	UNIT
Ψ_{JT}	Junction-to-top characterization parameter	19.1	22.5	°C/W
Ψ_{JB}	Junction-to-board characterization parameter	75.4	80.8	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	56.1	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the Semiconductor and IC Package Thermal Metrics application report.

5.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V_{CC}	T_A = 25°C			-40°C to 125°C			UNIT
			MIN	TYP	MAX	MIN	TYP	MAX	
V_{OH}	I_{OH} = –50µA	4.5V	4.4	4.5		4.4			V
	I_{OH} = –8mA	4.5V	3.94			3.8			
V_{OL}	I_{OL} = 50µA	4.5V			0.1			0.1	V
	I_{OL} = 8mA	4.5V			0.36			0.44	
I_I	V_I = 5.5V or GND and V_{CC} = 0V to 5.5V	0V to 5.5V			±0.1			±1	µA
I_{OZ}	V_O = V_{CC} or GND and V_{CC} = 5.5V	5.5V			±0.25			±2.5	µA
I_{CC}	V_I = V_{CC} or GND, I_O = 0, and V_{CC} = 5.5V	5.5V			4			40	µA
ΔI_{CC}	One input at 3.4V, Other inputs at V_{CC} or GND	5V			1.35			1.5	mA
C_I	V_I = V_{CC} or GND	5V		4	10			10	pF
C_O	V_O = V_{CC} or GND	5V		5					pF
C_{PD}	No load, F = 1MHz	5V		129					pF

5.6 Timing Characteristics

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	DESCRIPTION	CONDITION	V_{CC}	T_A = 25°C		-40°C to 125°C		UNIT
				MIN	MAX	MIN	MAX	
t_H	Hold time	SER after SRCLK↑	5V ± 0.5V	2		2		ns
t_{SU}	Setup time	SER before SRCLK↑	5V ± 0.5V	3		3		ns
t_{SU}	Setup time	SRCLK↑ before RCLK↑	5V ± 0.5V	5		5		ns
t_{SU}	Setup time	$\overline{SRCLR}$ high (inactive) before SRCLK↑	5V ± 0.5V	2.9		3.8		ns
t_{SU}	Setup time	$\overline{SRCLR}$ low before RCLK↑	5V ± 0.5V	5		5		ns
t_W	Pulse duration	RCLK or SRCLK high or low	5V ± 0.5V	5		5.5		ns
t_W	Pulse duration	$\overline{SRCLR}$ low	5V ± 0.5V	5		5.5		ns

5.7 Switching Characteristics

over operating free-air temperature range(unless otherwise noted). See *Parameter Measurement Information*

PARAMETER	FROM (INPUT)	TO (OUTPUT)	LOAD CAPACITANCE	V_{CC}	T_A = 25°C			-40°C to 125°C			UNIT
					MIN	TYP	MAX	MIN	TYP	MAX	
F_{MAX}	-	-	C_L = 15pF	5V ± 0.5V	135	175		115			MHz
t_{PZL}	$\overline{OE}$	Q	C_L = 15pF	5V ± 0.5V		5.4	8.6			12	ns
t_{PZH}	$\overline{OE}$	Q	C_L = 15pF	5V ± 0.5V		4.3	8.6			12	ns
t_{PLZ}	$\overline{OE}$	Q	C_L = 15pF	5V ± 0.5V		3.8	8	1		10.5	ns
t_{PHZ}	$\overline{OE}$	Q	C_L = 15pF	5V ± 0.5V		3.8	8	1		10.5	ns
t_{PLH}	RCLK	QA-QH	C_L = 15pF	5V ± 0.5V		4.3	7.4	1		9.5	ns
t_{PHL}	RCLK	QA-QH	C_L = 15pF	5V ± 0.5V		4.3	7.4	1		9.5	ns
t_{PLH}	SRCLK	QH'	C_L = 15pF	5V ± 0.5V		4.5	8.2	1		10.4	ns
t_{PHL}	SRCLK	QH'	C_L = 15pF	5V ± 0.5V		4.5	8.2	1		10.4	ns
t_{PHL}	$\overline{SRCLR}$	QH'	C_L = 15pF	5V ± 0.5V		4.5	8	1		10.1	ns
F_{MAX}	-	-	C_L = 50pF	5V ± 0.5V	120	140		95			MHz
t_{PZL}	$\overline{OE}$	Q	C_L = 50pF	5V ± 0.5V		6.8	10.6			14.4	ns
t_{PZH}	$\overline{OE}$	Q	C_L = 50pF	5V ± 0.5V		5.7	10.6			14.4	ns
t_{PLZ}	$\overline{OE}$	Q	C_L = 50pF	5V ± 0.5V		3.4	10.3			13.2	ns
t_{PHZ}	$\overline{OE}$	Q	C_L = 50pF	5V ± 0.5V		3.5	10.3			13.2	ns
t_{PLH}	RCLK	QA-QH	C_L = 50pF	5V ± 0.5V		5.6	9.4	1		11.5	ns
t_{PHL}	RCLK	QA-QH	C_L = 50pF	5V ± 0.5V		5.6	9.4	1		11.5	ns
t_{PLH}	SRCLK	QH'	C_L = 50pF	5V ± 0.5V		6.4	10.2	1		12.4	ns
t_{PHL}	SRCLK	QH'	C_L = 50pF	5V ± 0.5V		6.4	10.2	1		12.4	ns
t_{PHL}	$\overline{SRCLR}$	QH'	C_L = 50pF	5V ± 0.5V		6.4	10	1		12.1	ns

5.8 Noise Characteristics

V_{CC} = 5 V, C_L = 50 pF, T_A = 25°C

PARAMETER	DESCRIPTION	MIN	TYP	MAX	UNIT
$V_{OL(P)}$	Quiet output, maximum dynamic V_{OL}		0.2	0.8	V
$V_{OL(V)}$	Quiet output, minimum dynamic V_{OL}	-0.9	-0.2		V
$V_{OH(V)}$	Quiet output, minimum dynamic V_{OH}	4.4	4.7		V
$V_{IH(D)}$	High-level dynamic input voltage	2			V
$V_{IL(D)}$	Low-level dynamic input voltage			0.8	V

5.9 Typical Characteristics

T_A = 25°C (unless otherwise noted)

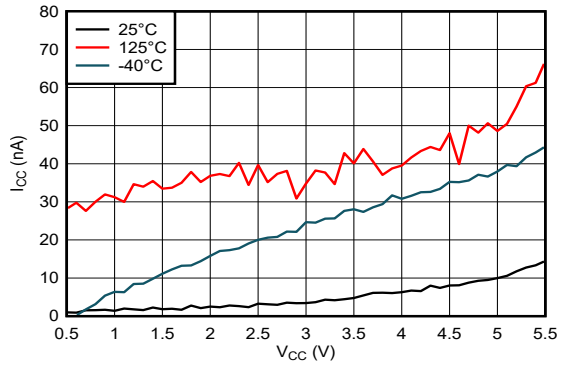


Figure 5-1. Supply Current Across Supply Voltage

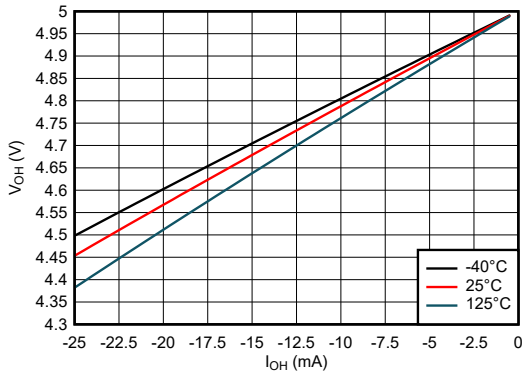


Figure 5-2. Output Voltage vs Current in HIGH State; 5V Supply

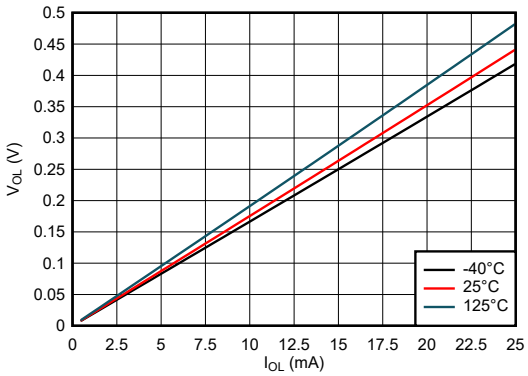


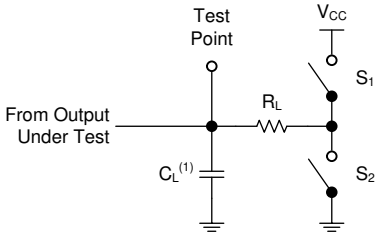
Figure 5-3. Output Voltage vs Current in LOW State; 5V Supply

6 Parameter Measurement Information

Phase relationships between waveforms were chosen arbitrarily for the examples listed in the following table. All input pulses are supplied by generators having the following characteristics: PRR ≤ 1MHz, Z_O = 50Ω, t_t < 2.5ns.

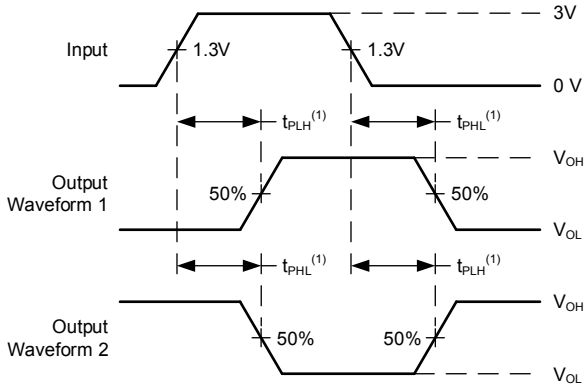
The outputs are measured individually with one input transition per measurement.

TEST	S1	S2	R_L	C_L	ΔV	V_{CC}
t_{PLH}, t_{PHL}	OPEN	OPEN	—	15pF, 50pF	—	ALL
t_{PLZ}, t_{PZL}	CLOSED	OPEN	1 kΩ	15pF, 50pF	0.15V	≤ 2.5V
t_{PHZ}, t_{PZH}	OPEN	CLOSED	1 kΩ	15pF, 50pF	0.15V	≤ 2.5V
t_{PLZ}, t_{PZL}	CLOSED	OPEN	1 kΩ	15pF, 50pF	0.3V	> 2.5V
t_{PHZ}, t_{PZH}	OPEN	CLOSED	1 kΩ	15pF, 50pF	0.3V	> 2.5V



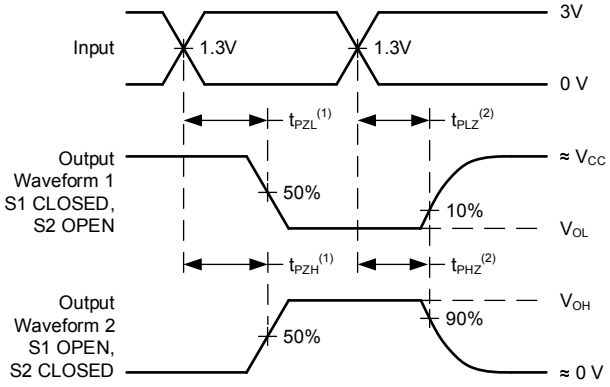
(1) C_L includes probe and test-fixture capacitance.

Figure 6-1. Load Circuit for 3-State Outputs



(1) The greater between t_{PLH} and t_{PHL} is the same as t_{pd}.

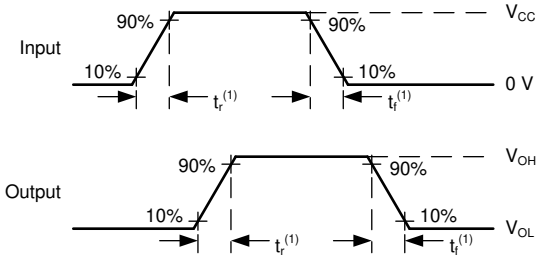
Figure 6-2. Voltage Waveforms Propagation Delays



(1) The greater between t_{PZL} and t_{PZH} is the same as t_{en}.

(2) The greater between t_{PLZ} and t_{PHZ} is the same as t_{dis}.

Figure 6-3. Voltage Waveforms Propagation Delays



(1) The greater between t_r and t_f is the same as t_t.

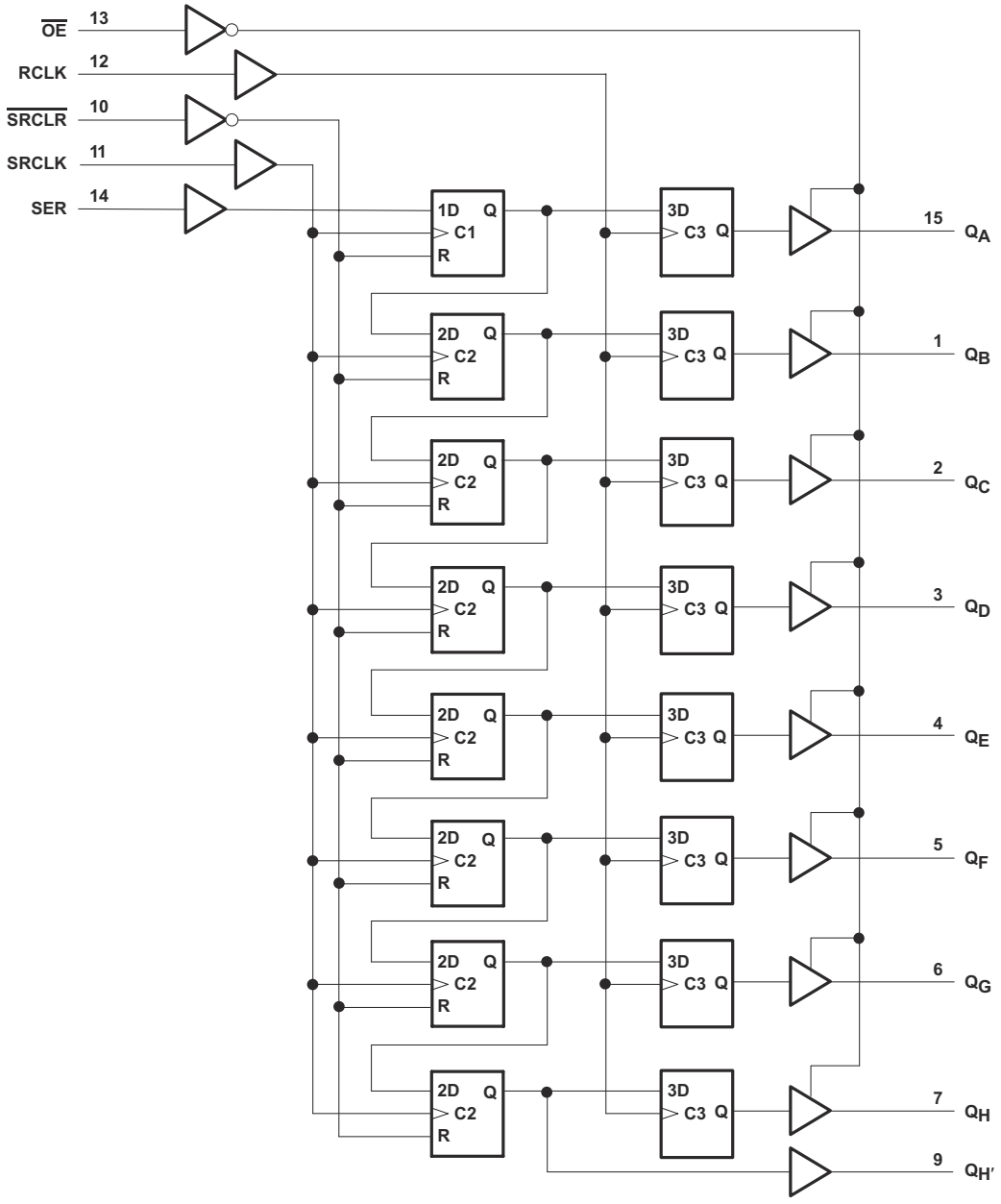
Figure 6-4. Voltage Waveforms, Input and Output Transition Times

7 Detailed Description

7.1 Overview

The SN74AHCT595-Q1 devices contain an 8-bit serial-in, parallel-out shift register that feeds an 8-bit D-type storage register. The storage register has parallel 3-state outputs. Separate clocks are provided for the shift and storage registers. The shift register has a direct overriding clear ($\overline{SRCLR}$) input, serial (SER) input, and serial outputs for cascading. When the output-enable ($\overline{OE}$) input is high, the outputs are in the high-impedance state. Both the shift register clock (SRCLK) and storage register clock (RCLK) are positive-edge triggered. If both clocks are connected together, then the shift register always is one clock pulse ahead of the storage register.

7.2 Functional Block Diagram



Pin numbers shown are for the PW and BQB packages.

7.3 Feature Description

7.3.1 Balanced CMOS 3-State Outputs

This device includes balanced CMOS 3-state outputs. Driving high, driving low, and high impedance are the three states that these outputs can be in. The term *balanced* indicates that the device can sink and source similar currents. The drive capability of this device may create fast edges into light loads, so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device can drive larger currents than the device can sustain without being damaged. It is important for the output power of the device to be limited to avoid damage due to overcurrent. The electrical and thermal limits defined in the *Absolute Maximum Ratings* must be followed at all times.

When placed into the high-impedance state, the output will neither source nor sink current, with the exception of minor leakage current as defined in the *Electrical Characteristics* table. In the high-impedance state, the output voltage is not controlled by the device and is dependent on external factors. If no other drivers are connected to the node, then this is known as a floating node and the voltage is unknown. A pull-up or pull-down resistor can be connected to the output to provide a known voltage at the output while it is in the high-impedance state. The value of the resistor will depend on multiple factors, including parasitic capacitance and power consumption limitations. Typically, a 10kΩ resistor can be used to meet these requirements.

Unused 3-state CMOS outputs should be left disconnected.

7.3.2 Latching Logic

This device includes latching logic circuitry. Latching circuits commonly include D-type latches and D-type flip-flops, but include all logic circuits that act as volatile memory.

When the device is powered on, the state of each latch is unknown. There is no default state for each latch at start-up.

The output state of each latching logic circuit only remains stable as long as power is applied to the device within the supply voltage range specified in the *Recommended Operating Conditions* table.

7.3.3 TTL-Compatible CMOS Inputs

This device includes TTL-compatible CMOS inputs. These inputs are specifically designed to interface with TTL logic devices by having a reduced input voltage threshold.

TTL-compatible CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the *Electrical Characteristics*. The worst case resistance is calculated with the maximum input voltage, given in the *Absolute Maximum Ratings*, and the maximum input leakage current, given in the *Electrical Characteristics*, using Ohm's law (R = V ÷ I).

TTL-compatible CMOS inputs require that input signals transition between valid logic states quickly, as defined by the input transition time or rate in the *Recommended Operating Conditions* table. Failing to meet this specification will result in excessive power consumption and could cause oscillations. More details can be found in the *Implications of Slow or Floating CMOS Inputs* application report.

Do not leave TTL-compatible CMOS inputs floating at any time during operation. Unused inputs must be terminated at V_{CC} or GND. If a system will not be actively driving an input at all times, a pull-up or pull-down resistor can be added to provide a valid input voltage during these times. The resistor value will depend on multiple factors; however, a 10kΩ resistor is recommended and typically will meet all requirements.

7.3.4 Wettable Flanks

This device includes wettable flanks for at least one package. See the *Features* section on the front page of the data sheet where packages include this feature.

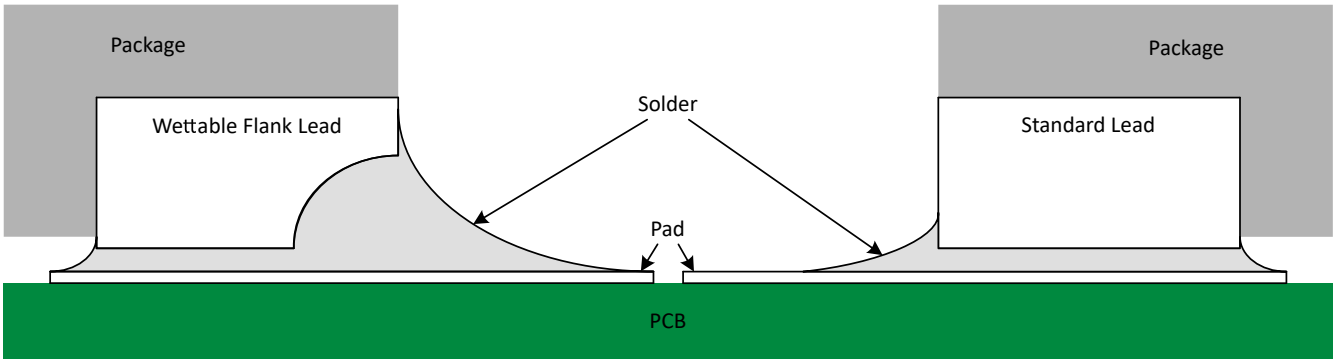


Figure 7-1. Simplified Cutaway View of Wettable-Flank QFN Package and Standard QFN Package After Soldering

Wettable flanks help improve side wetting after soldering, which makes QFN packages easier to inspect with automatic optical inspection (AOI). As shown in Figure 7-1, a wettable flank can be dimpled or step-cut to provide additional surface area for solder adhesion which assists in reliably creating a side fillet. See the mechanical drawing for additional details.

7.3.5 Clamp Diode Structure

As Figure 7-2 shows, the outputs to this device have both positive and negative clamping diodes, and the inputs to this device have negative clamping diodes only.

CAUTION

Voltages beyond the values specified in the *Absolute Maximum Ratings* table can cause damage to the device. The input and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

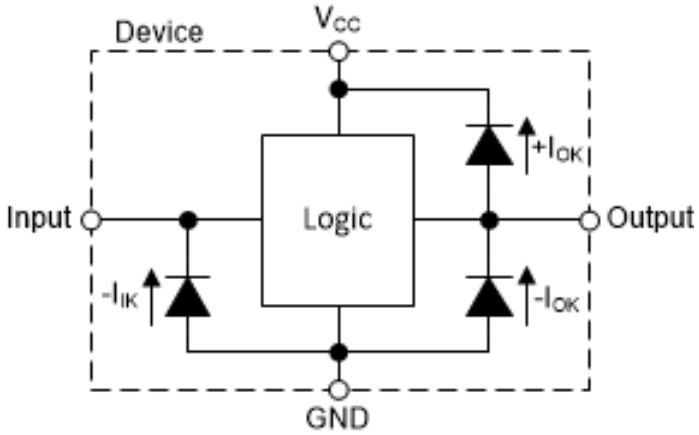


Figure 7-2. Electrical Placement of Clamping Diodes for Each Input and Output

7.4 Device Functional Modes

Table 7-1. Function Table

INPUTS					FUNCTION
SER	SRCLK	$\overline{\text{SRCLR}}$	RCLK	$\overline{\text{OE}}$	
X	X	X	X	H	Outputs Q_A – Q_H are disabled.
X	X	X	X	L	Outputs Q_A – Q_H are enabled.
X	X	L	X	X	Shift register is cleared.
L	↑	H	X	X	First stage of the shift register goes low. Other stages store the data of previous stage, respectively.
H	↑	H	X	X	First stage of the shift register goes high. Other stages store the data of previous stage, respectively.
X	X	X	↑	X	Shift-register data is stored in the storage register.

8 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

8.1 Application Information

The SN74AHCT595-Q1 is a low-drive CMOS device that can be used for a multitude of bus interface type applications where output ringing is a concern. The low drive and slow edge rates will minimize overshoot and undershoot on the outputs. The input switching levels have been lowered to accommodate TTL inputs of 0.8V V_{IL} and 2V V_{IH}. This feature makes it an excellent choice for translating up from 3.3V to 5V. Figure 8-1 shows this type of translation.

8.2 Typical Application

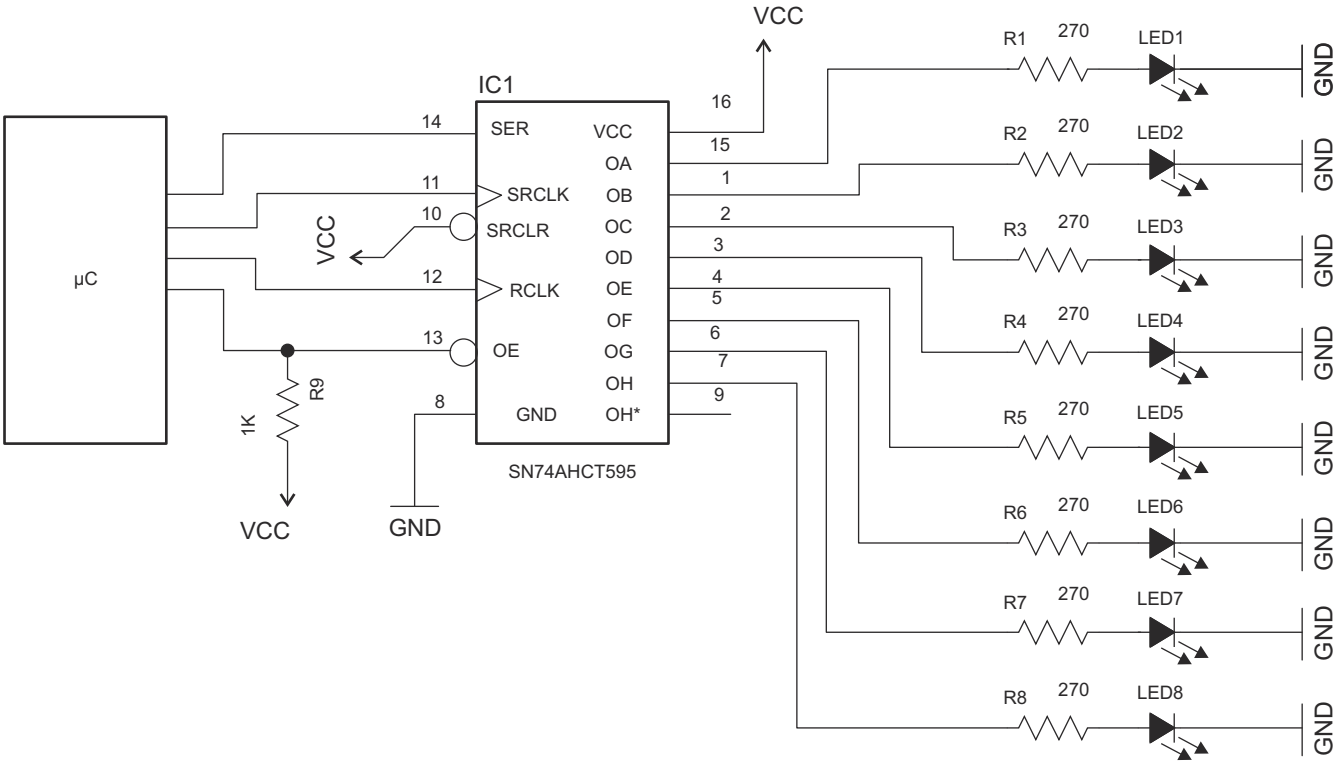


Figure 8-1. Specific Application Schematic

8.2.1 Design Requirements

This device uses CMOS technology and has balanced output drive. Take care to avoid bus contention because it can drive currents that would exceed maximum limits. The high drive will also create fast edges into light loads so routing and load conditions should be considered to prevent ringing.

8.2.2 Detailed Design Procedure

- Recommended input conditions
  - Specified high and low levels. See (V_{IH} and V_{IL}) in the *Recommended Operating Conditions* table.
  - Specified high and low levels. See (V_{IH} and V_{IL}) in the *Recommended Operating Conditions* table.
  - Inputs are overvoltage tolerant allowing them to go as high as 5.5V at any valid V_{CC}

- Recommend output conditions
  - Load currents should not exceed 25mA per output and 50mA total for the part
  - Outputs should not be pulled above V_{CC}

8.2.3 Application Curves

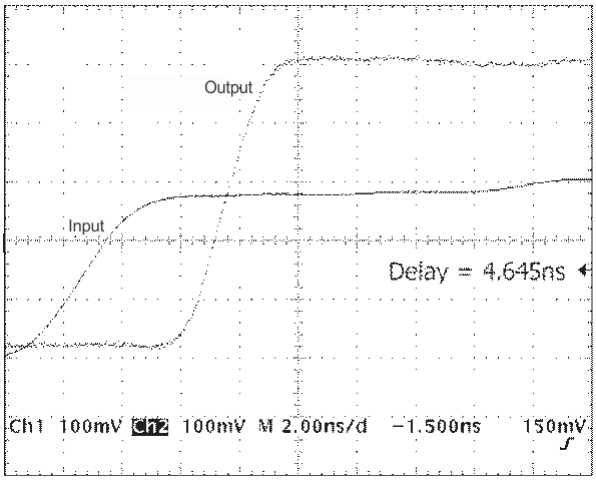


Figure 8-2. Typical Application Curve

8.3 Power Supply Recommendations

The power supply can be any voltage between the MIN and MAX supply voltage rating located in the *Recommended Operating Conditions* table.

Each V_{CC} pin should have a good bypass capacitor to prevent power disturbance. For devices with a single supply, 0.1µF is recommended; if there are multiple V_{CC} pins, then 0.01µF or 0.022µF is recommended for each power pin. It is acceptable to parallel multiple bypass capacitors to reject different frequencies of noise. A 0.1µF and a 1µF are commonly used in parallel. The bypass capacitor should be installed as close to the power pin as possible for best results.

8.4 Layout

8.4.1 Layout Guidelines

When using multiple-bit logic devices, inputs should never float.

In many cases, functions or parts of functions of digital logic devices are unused; for example, when only two inputs of a triple-input AND gate are used or only 3 of the 4 buffer gates are used. Such input pins should not be left unconnected because the undefined voltages at the outside connections result in undefined operational states. Figure 8-3 specifies the rules that must be observed under all circumstances. All unused inputs of digital logic devices must be connected to a high or low bias to prevent them from floating. The logic level that should be applied to any particular unused input depends on the function of the device. Generally they will be tied to GND or V_{CC}, whichever makes more sense or is more convenient. It is generally acceptable to float outputs, unless the part is a transceiver. If the transceiver has an output enable pin, it will disable the output section of the part when asserted. This will not disable the input section of the I/Os, so they cannot float when disabled.

8.4.2 Layout Example

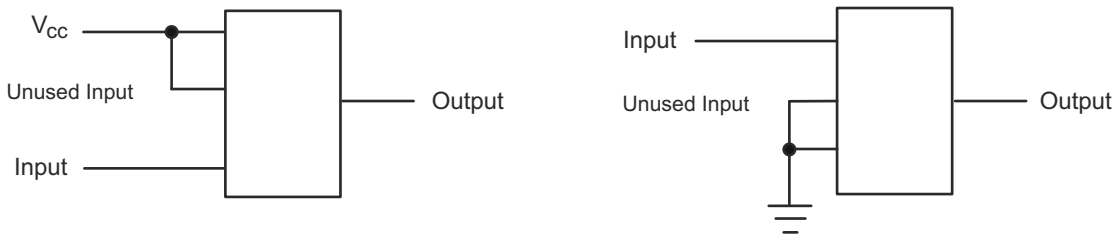


Figure 8-3. Layout Diagram

9 Device and Documentation Support

9.1 Documentation Support

9.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, *CMOS Power Consumption and Cpd Calculation*
- Texas Instruments, *Implications of Slow or Floating CMOS Inputs*
- Texas Instruments, *Thermal Characteristics of Standard Linear and Logic (SLL) Packages and Devices*
- Texas Instruments, *Understanding Schmitt Triggers*

9.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on *Notifications* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

9.3 Support Resources

TI E2E™ support forums are an engineer's go-to source for fast, verified answers and design help — straight from the experts. Search existing answers or ask your own question to get the quick design help you need.

Linked content is provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

9.4 Trademarks

TI E2E™ is a trademark of Texas Instruments.
All trademarks are the property of their respective owners.

9.5 Electrostatic Discharge Caution

This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

9.6 Glossary

TI Glossary	This glossary lists and explains terms, acronyms, and definitions.

10 Revision History

NOTE: Page numbers for previous revisions may differ from page numbers in the current version.

DATE	REVISION	NOTES
March 2024	*	Initial Release

11 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CAHCT595QWBQBRQ1	ACTIVE	WQFN	BQB	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AT595Q	Samples
SN74AHCT595QPWRQ1	ACTIVE	TSSOP	PW	16	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	AHT595Q	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

OTHER QUALIFIED VERSIONS OF SN74AHCT595-Q1 :

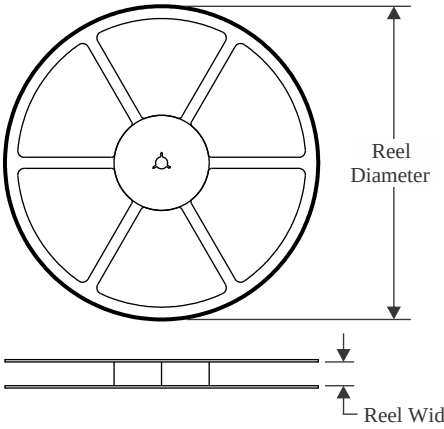
- Catalog : SN74AHCT595

NOTE: Qualified Version Definitions:

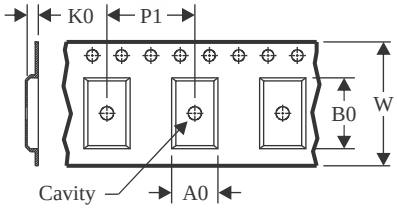
- Catalog - TI's standard catalog product

TAPE AND REEL INFORMATION

REEL DIMENSIONS

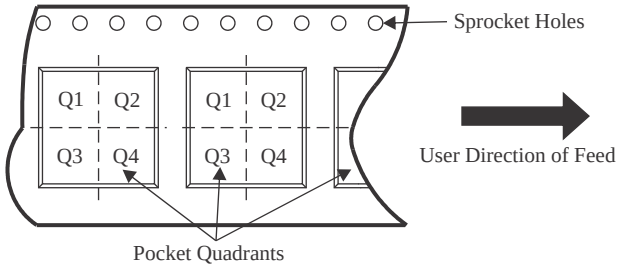


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

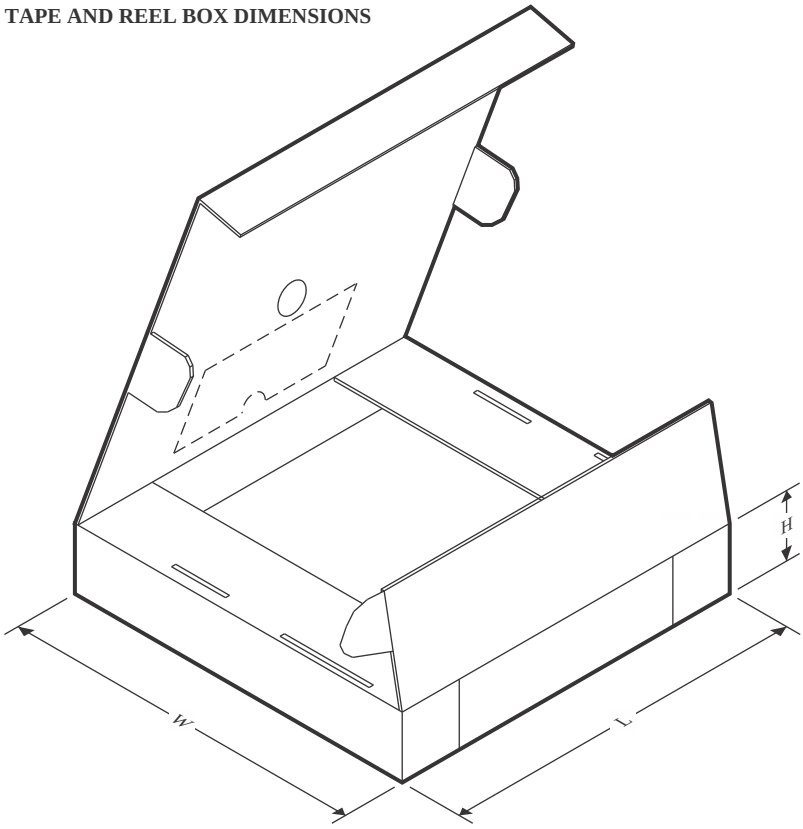
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CAHCT595QWBQBRQ1	WQFN	BQB	16	3000	180.0	12.4	2.8	3.8	1.2	4.0	12.0	Q1
SN74AHCT595QPWRQ1	TSSOP	PW	16	3000	330.0	12.4	6.9	5.6	1.6	8.0	12.0	Q1

TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

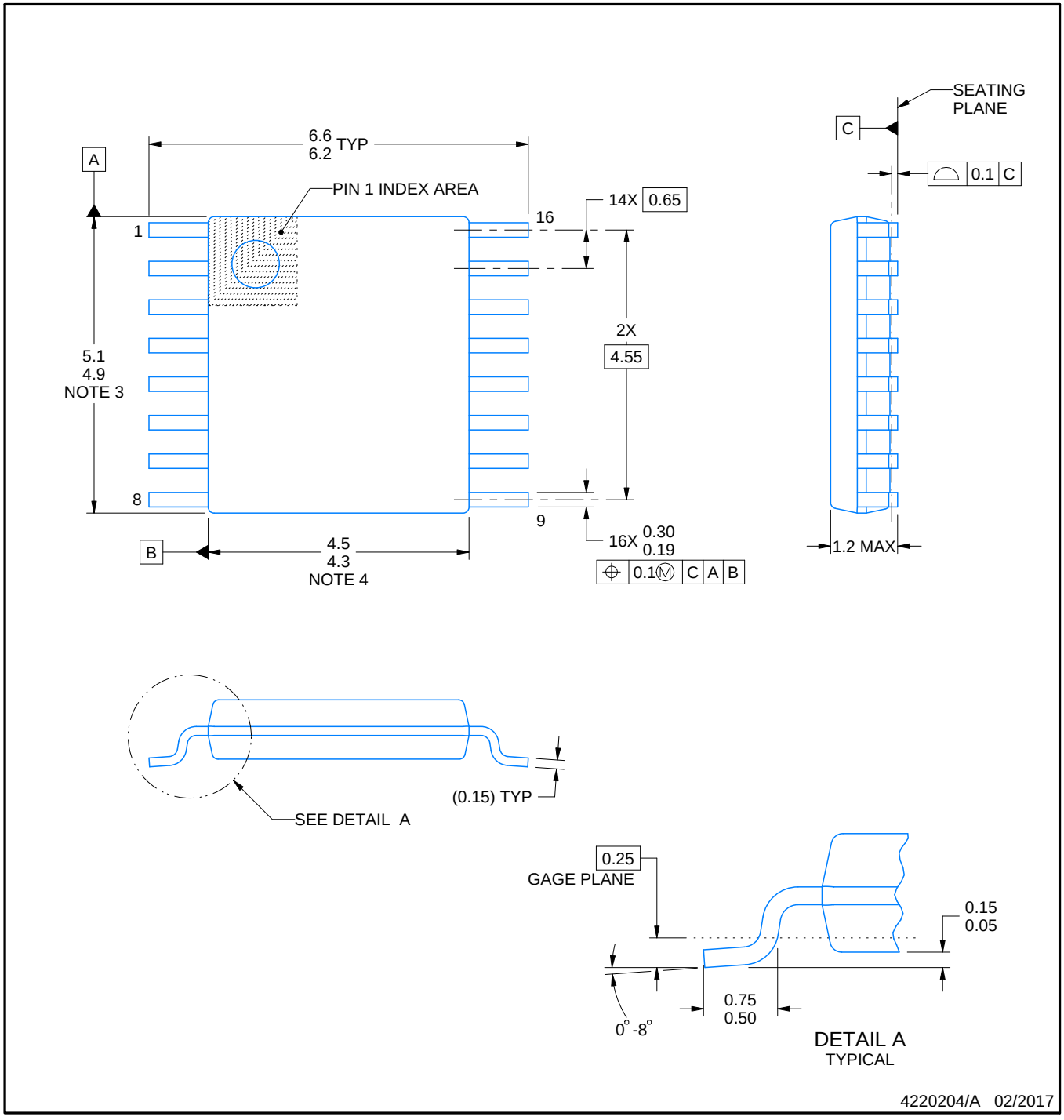
Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CAHCT595QWBQBRQ1	WQFN	BQB	16	3000	210.0	185.0	35.0
SN74AHCT595QPWRQ1	TSSOP	PW	16	3000	356.0	356.0	35.0

PACKAGE OUTLINE

PW0016A

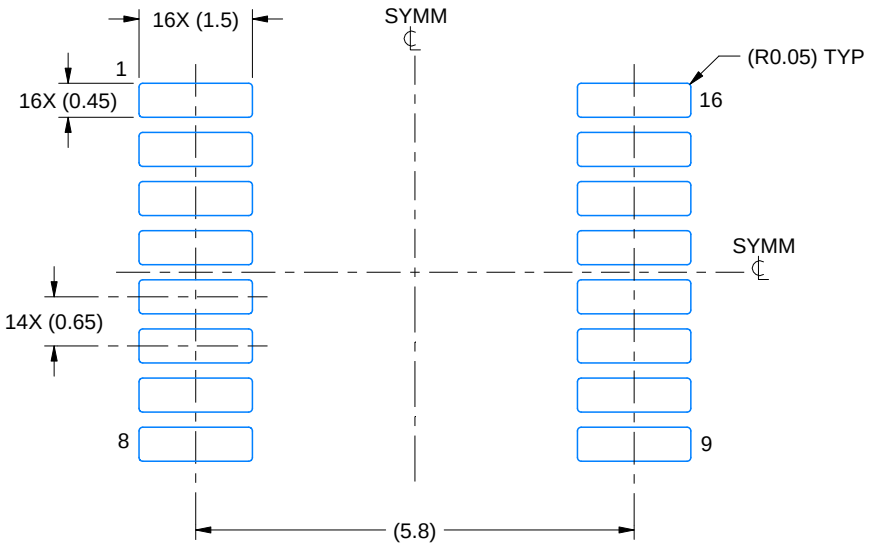
TSSOP - 1.2 mm max height

SMALL OUTLINE PACKAGE

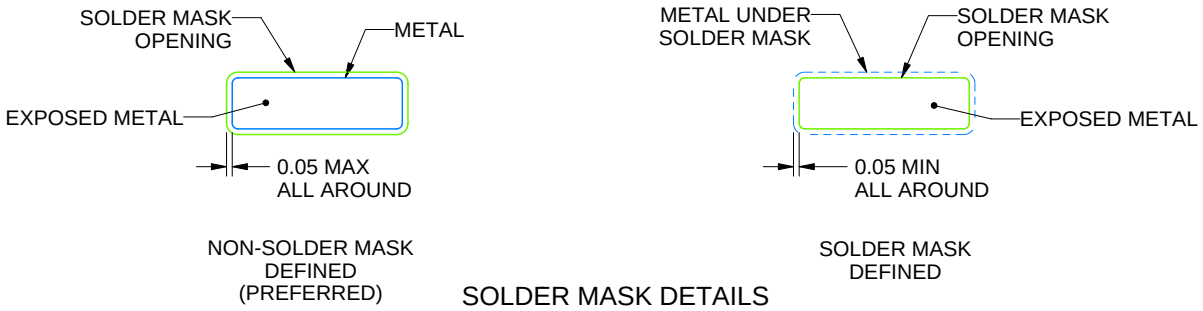


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.15 mm per side.
4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
5. Reference JEDEC registration MO-153.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 10X

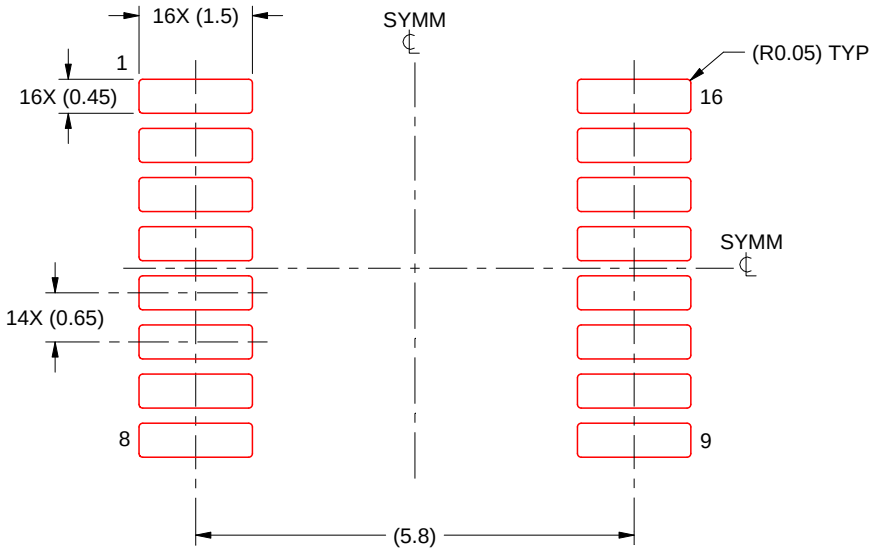


SOLDER MASK DETAILS

4220204/A 02/2017

NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.
7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL
SCALE: 10X

4220204/A 02/2017

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
9. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

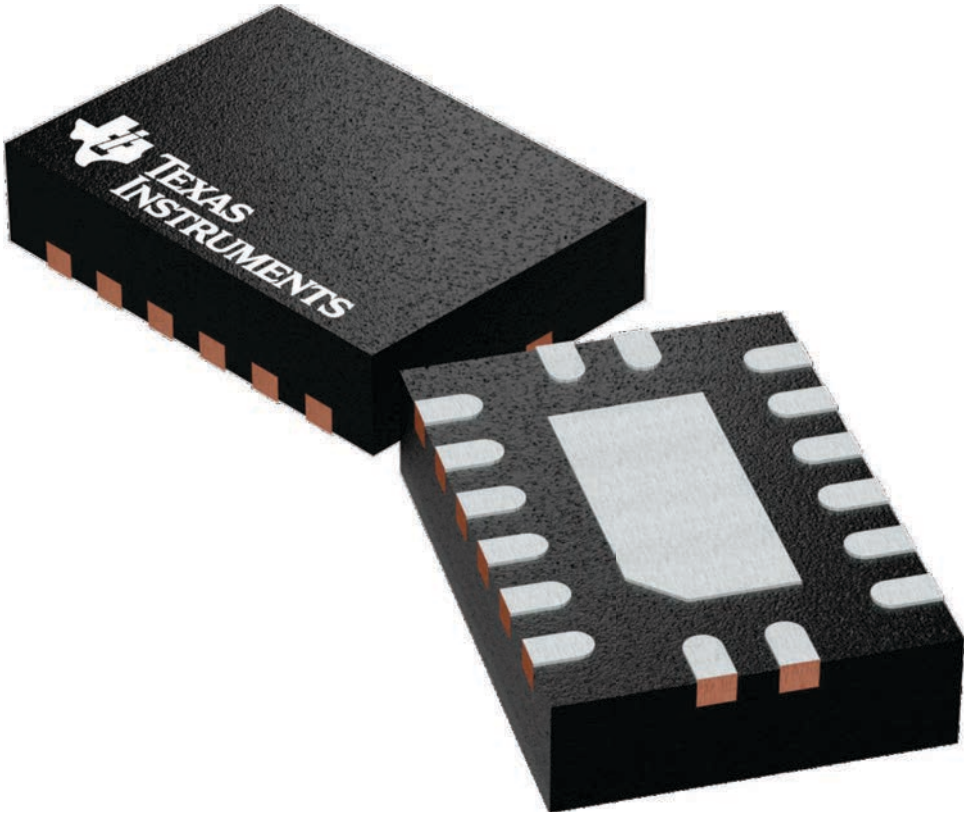
BQB 16

WQFN - 0.8 mm max height

2.5 x 3.5, 0.5 mm pitch

PLASTIC QUAD FLATPACK - NO LEAD

This image is a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.



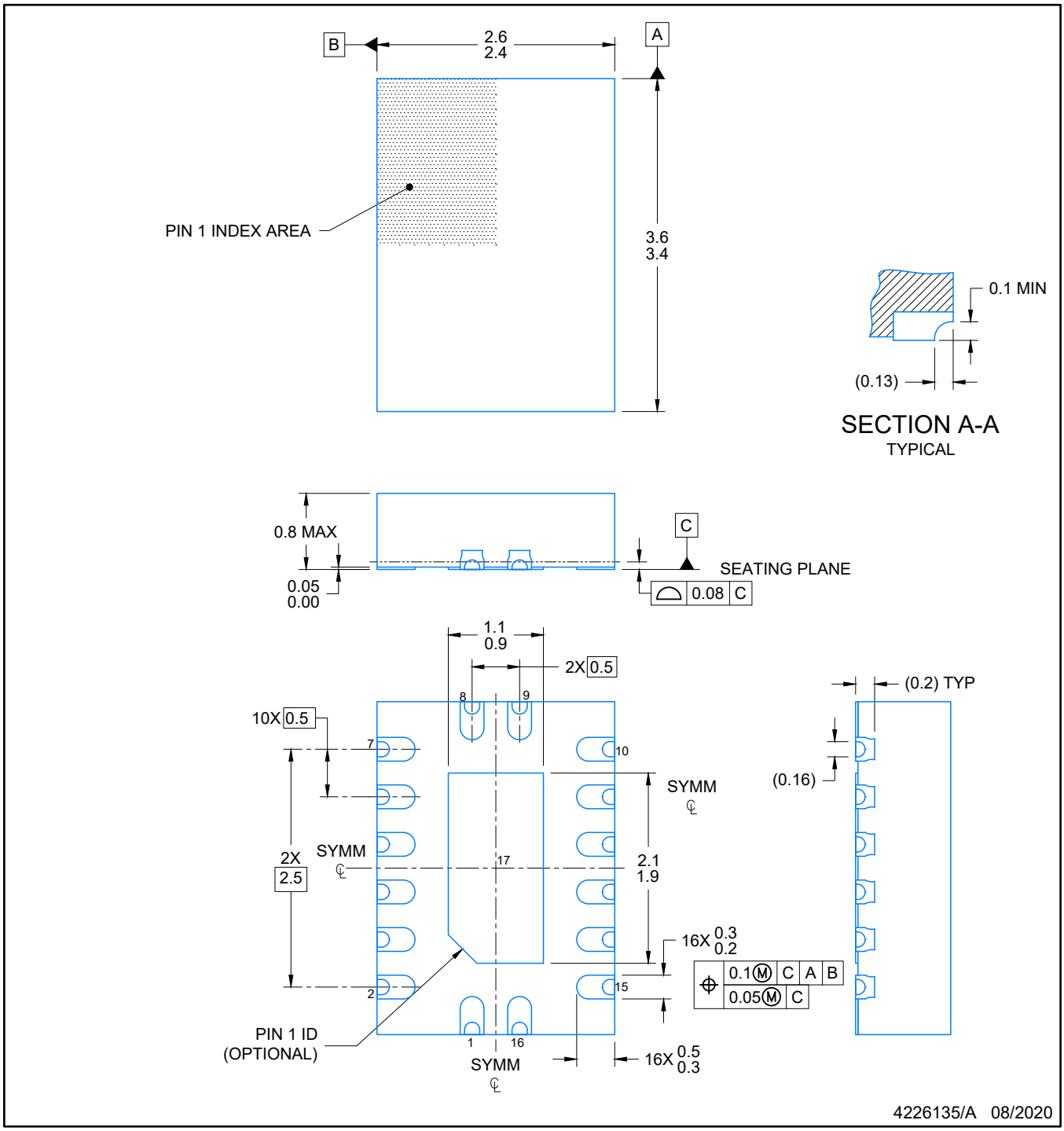
4226161/A

PACKAGE OUTLINE

BQB0016B

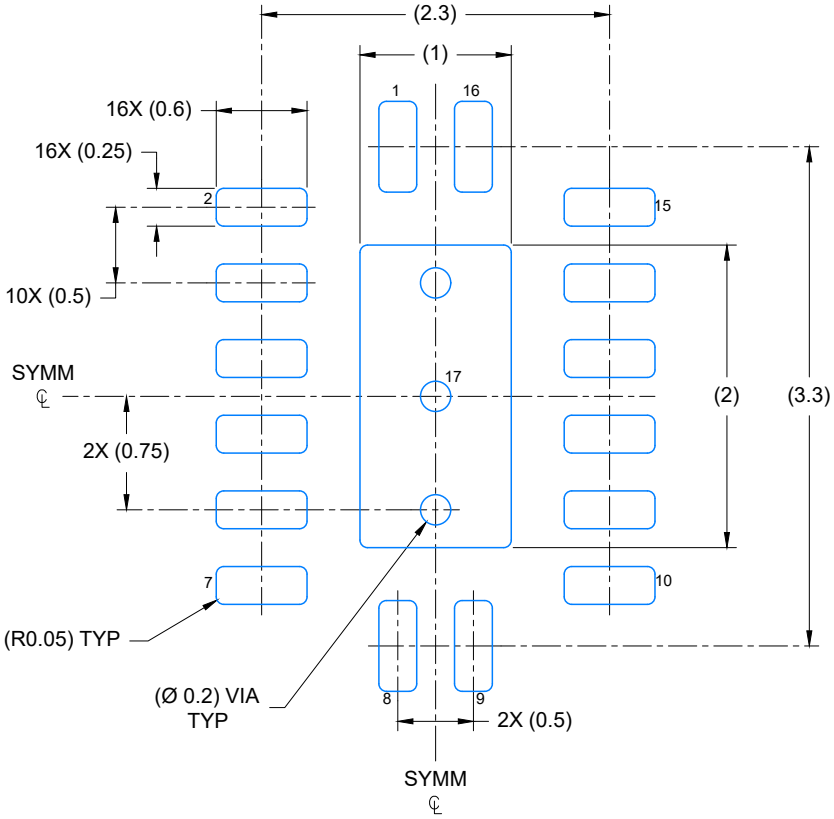
WQFN - 0.8 mm max height

INDSTNAME



NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.

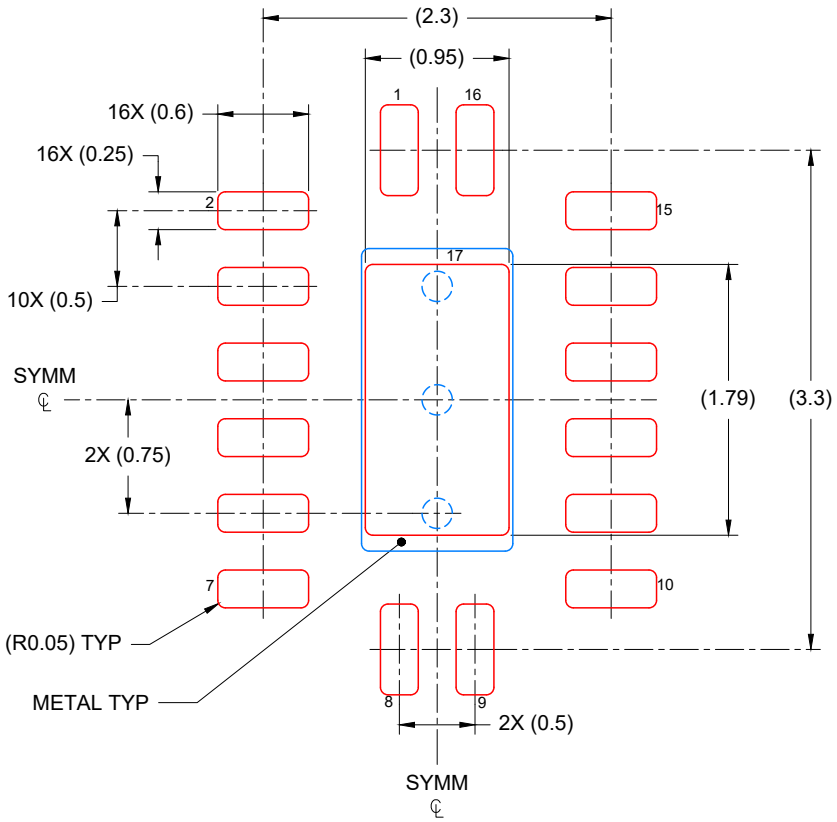


LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD
85% PRINTED COVERAGE BY AREA
SCALE: 20X

4226135/A 08/2020

NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

IMPORTANT NOTICE AND DISCLAIMER

TI PROVIDES TECHNICAL AND RELIABILITY DATA (INCLUDING DATA SHEETS), DESIGN RESOURCES (INCLUDING REFERENCE DESIGNS), APPLICATION OR OTHER DESIGN ADVICE, WEB TOOLS, SAFETY INFORMATION, AND OTHER RESOURCES “AS IS” AND WITH ALL FAULTS, AND DISCLAIMS ALL WARRANTIES, EXPRESS AND IMPLIED, INCLUDING WITHOUT LIMITATION ANY IMPLIED WARRANTIES OF MERCHANTABILITY, FITNESS FOR A PARTICULAR PURPOSE OR NON-INFRINGEMENT OF THIRD PARTY INTELLECTUAL PROPERTY RIGHTS.

These resources are intended for skilled developers designing with TI products. You are solely responsible for (1) selecting the appropriate TI products for your application, (2) designing, validating and testing your application, and (3) ensuring your application meets applicable standards, and any other safety, security, regulatory or other requirements.

These resources are subject to change without notice. TI grants you permission to use these resources only for development of an application that uses the TI products described in the resource. Other reproduction and display of these resources is prohibited. No license is granted to any other TI intellectual property right or to any third party intellectual property right. TI disclaims responsibility for, and you will fully indemnify TI and its representatives against, any claims, damages, costs, losses, and liabilities arising out of your use of these resources.

TI’s products are provided subject to TI’s Terms of Sale or other applicable terms available either on ti.com or provided in conjunction with such TI products. TI’s provision of these resources does not expand or otherwise alter TI’s applicable warranties or warranty disclaimers for TI products.

TI objects to and rejects any additional or different terms you may have proposed.

Mailing Address: Texas Instruments, Post Office Box 655303, Dallas, Texas 75265